

AMENDMENTS TO THE SPECIFICATION**In the Specification**

Please replace the paragraph beginning on line 14 of page 9 with the following amended paragraph:

CVD tool 340 includes multiple CVD chambers 342. ~~[[Annealing]]~~ At least one annealing chamber 332 is provided on CVD tool 340. Annealing chamber 332 can be attached to or can replace a CVD chamber 342 of CVD tool 340. A wafer being processed will have a metal such as copper deposited by CVD in one of the CVD chambers 342. After the metal deposition process, the wafer is moved to annealing chamber 332, which is provided on CVD tool 340. Because annealing chamber 332 is integrated into CVD tool 340, the annealing process can begin almost immediately to avoid the degradation of the deposited metal. After the wafer has undergone annealing in the annealing chamber 332, it is transferred to the CMP tool 320 and onto one of the CMP platforms 322.

Please replace the paragraph beginning on line 1 of page 10 with the following amended paragraph:

FIGURE 4 shows yet another embodiment in which a wafer processing apparatus 400 includes a metal deposition tool 460 and a CMP tool 420. In the embodiment shown in FIGURE 4, metal deposition tool 460 includes metal deposition chambers 462. Metal deposition tool 460 can be an electroplating tool or a CVD tool, for example. Also, a metal deposition tool need not have multiple metal deposition chambers 462. ~~[[Annealing]]~~ At least one annealing chamber 432 is integrated into the CMP tool 420 in the embodiment illustrated in FIGURE 4. CMP tool 420 includes CMP platforms 422. During processing, the wafer is transferred from metal deposition tool 460 into annealing

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chamber 432, which is on CMP tool 420 in this embodiment. After annealing in annealing chamber 432, the wafer is transferred almost immediately to a CMP platform 422 to undergo the CMP process. In this case, the amount of time between the end of the annealing process and the beginning of the CMP process can be controlled.